

IPG20N10S4L22AATMA1

IPG20N10S4L22AATMA1 Information



Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



IPG20N10S4L22AATMA1 Specifications

Manufacturer Part Number	IPG20N10S4L22AATMA1
Manufacturer	Infineon Technologies
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Arrays
Package	8-PowerVDFN
Series	OptiMOS?
FET Type	2 N-Channel (Dual)
FET Feature	Logic Level Gate
Drain to Source Voltage (Vdss)	100V
Current - Continuous Drain (Id) @ 25°C	20A
Rds On (Max) @ Id, Vgs	22 mOhm @ 17A, 10V
Vgs(th) (Max) @ Id	2.1V @ 25µA
Gate Charge (Qg) (Max) @ Vgs	27nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	1755pF @ 25V
Power - Max	60W
Operating Temperature	-55°C ~ 175°C (TJ)
Mounting Type	Surface Mount
Package / Case	8-PowerVDFN
Supplier Device Package	PG-TDSON-8-10
	Report errors?

IPG20N10S4L22AATMA1 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE BUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

IPG20N10S4L22AATMA1 Payment Methods



If you have any question about IPG20N10S4L22AATMA1, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com